

METHOD OF PREVENTING AUTODOPING

ABSTRACT

A method of making a silicon-based electronic device is provided. The method includes, for example, the steps of forming a doped silicon layer on a surface of a substrate material and forming an undoped silicon capping layer on the doped silicon layer. The thin "capping" layers of undoped silicon prevent outgassing of the dopants underneath the cap. In this manner, the next deposition of doped silicon is not subject to autodoping by the previous doped silicon deposition.